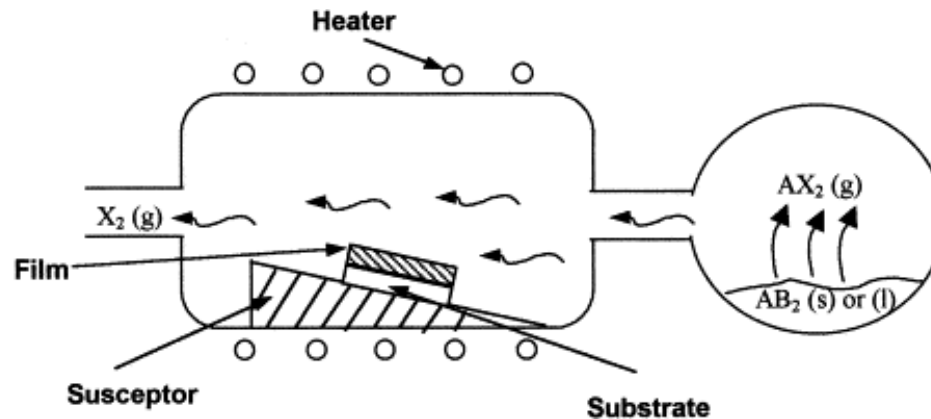


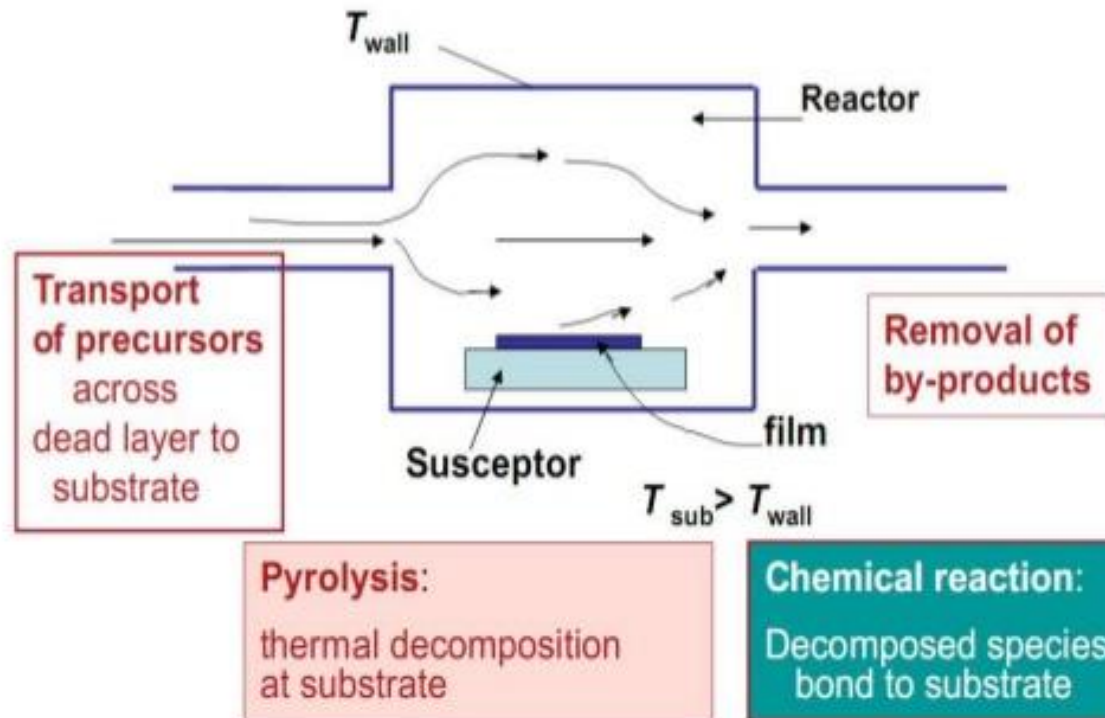
# Chemical Vapour Deposition (CVD)\*

\* CVD is coating of a preheated substrate with desired metal in metallic or compound form by using a vaporizable compound of the metal which forwards to vacuum chamber with a carrier reactive gas.



Prof. Dr. Kerem Altuğ GÜLER

# STEPS INVOLVED IN A CVD PROCESS (SCHEMATIC)



- CVD is an old multifunctional technique is used for either carbon, silicon, carbides, nitrides, oxides and intermetallic coatings to suitable substrates or powder and fiber production.
- In present, this technology is especially used for production of semi-conductors and electronic components.

## Process parameters of conventional CVD process

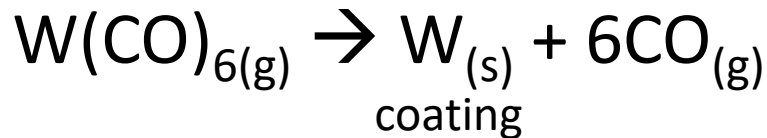
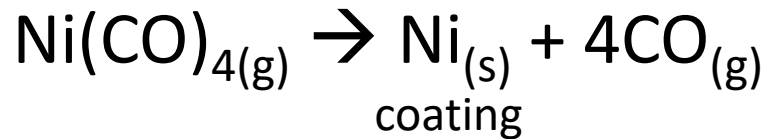
- Temperature: 800 – 2000°C
- Pressure:  $10^{-6}$  to 1 atmosphere (atm)
- Precursors:
  - Reactive gasses: Metal halides\*, carbonyls\*\*
  - Reducing gasses:  $H_2$
  - Inert gasses: Ar,  $N_2$
  - Other gasses:  $CH_4$ ,  $CO_2$ ,  $NH_3$  and other hydrocarbon gasses.

Halide\* (salt): It is a binary compound of a halogen (AgF, AgCl)

Carbonyl\*\* group: Carbon atom double bonded to oxygen atom (C=O).

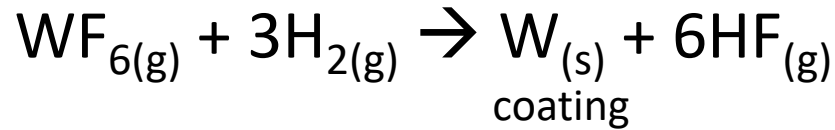
**In CVD, there are several reactions occur during deposition. Examples of these reactions:**

**1- Thermal decomposition:**



- Carbonyls decompose under 200 °C. For better adherence substrate is heated up to 800-1000 °C.
- The most important disadvantage of carbonyls is being highly toxic.
- Decomposition of halides ( $\text{WF}_6$ ) and hydrides ( $\text{B}_2\text{H}_6$ ) occurs over 500 °C. So process temperature must be high.

## 2- Reduction:



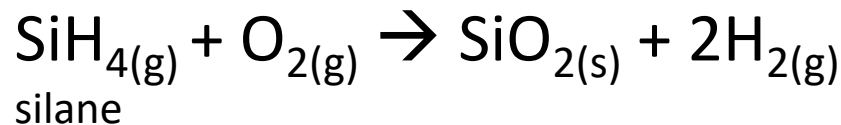
Working temperatures:

- Ti  $\rightarrow$  1100 °C
- Mo and W  $\rightarrow$  600 – 700 °C

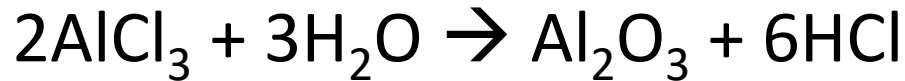
## 3- Oxidation:



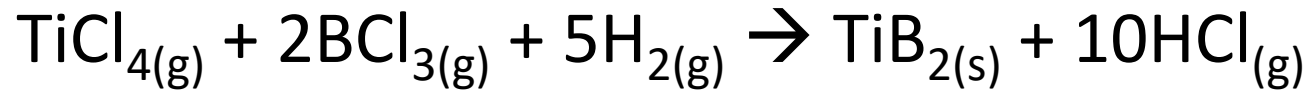
- SiO<sub>2</sub> also can be deposited with oxidation of silane gas in lower temperatures (450°C).



#### 4- Hydrolysis



#### 5- Co-reduction (birlikte indirgenme)



# Advantages of CVD technique

- Capability of production and decomposition of ultra dense and pure materials.
- Complex shaped parts can be coated uniformly.
- Conformal\* and multifunctional coatings can be obtained.
- Deposition rate can be easily adjust.
  - Low deposition rates are preferred for epitaxial\*\* thin film growths of microelectronic applications.
  - High deposition rates are preferred for deposition of thick protective coatings.

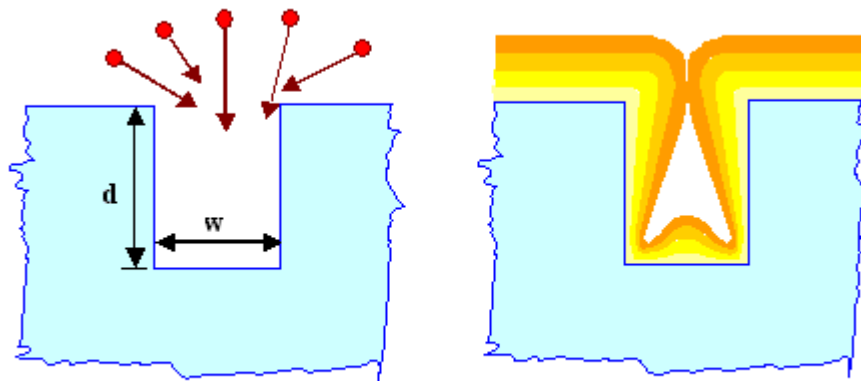
\*Conformal: Polymeric thin films for protection of PCB.

\*\*Epitaxy: The process of growing a crystal of a particular orientation on top of another crystal, where the orientation is determined by the underlying crystal.

- Depositions can be carried out at low substrate temperatures. Dense coatings which covers whole surface or field selective coatings can be obtained. This is only possible with CVD.
- High melting point materials can be coated at lower temperatures. E.g. Refractory materials like SiC can be deposited at 1000 °C.
- Various kinds of chemical precursors can be used.
- Capability of controlling crystal structure, surface morphology and orientation of CVD products by controlling process parameters.

## Disadvantages of CVD technique

- The most significant disadvantages of conventional CVD technique is necessity of substrate heating up to 800 – 1000 °C. E.g. High speed steels can not be coated with conventional CVD.
- Input and output gasses may be in toxic, corrosive, flammable and/or explosive properties. Thus it can be dangerous and unsafe.
- It is not suitable for material mixtures.
- Excessive reactive gasses can create keyhole\*.



Idealized Contact Hole



\*Keyhole formation

# Applications of CVD technique

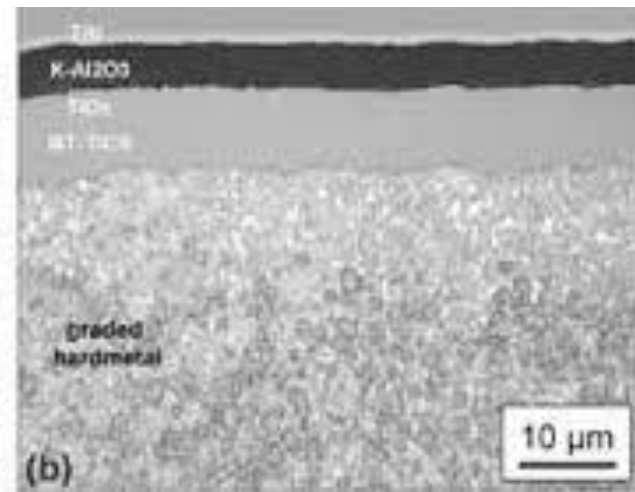
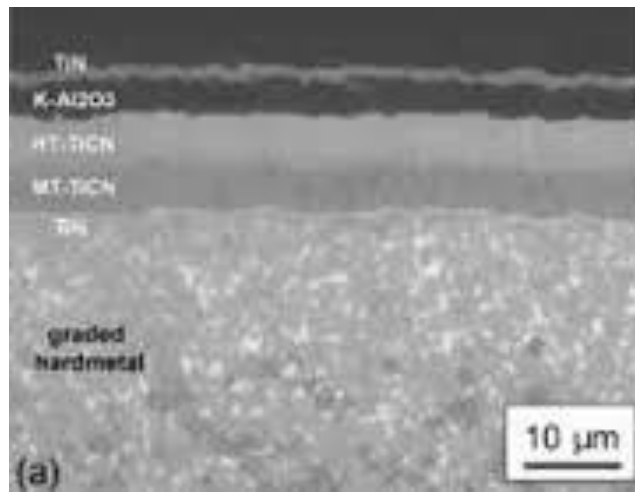
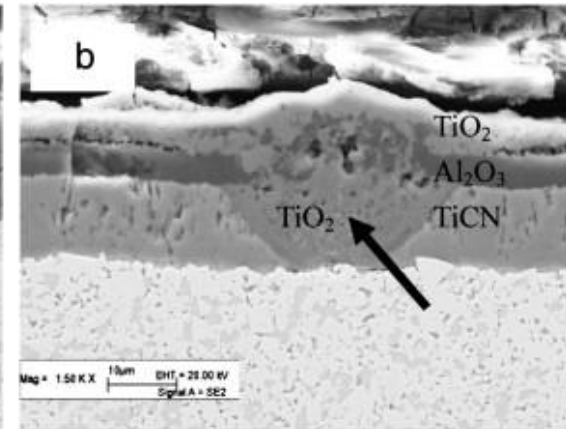
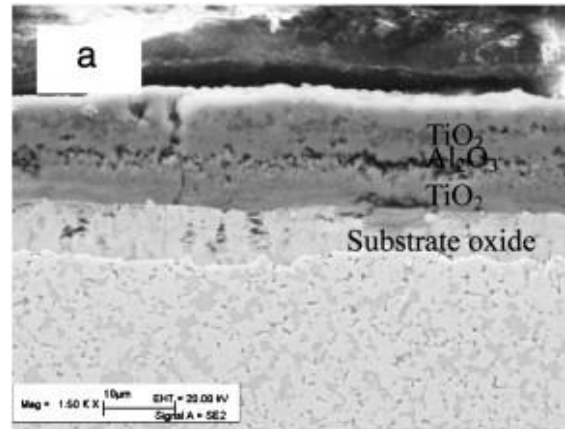
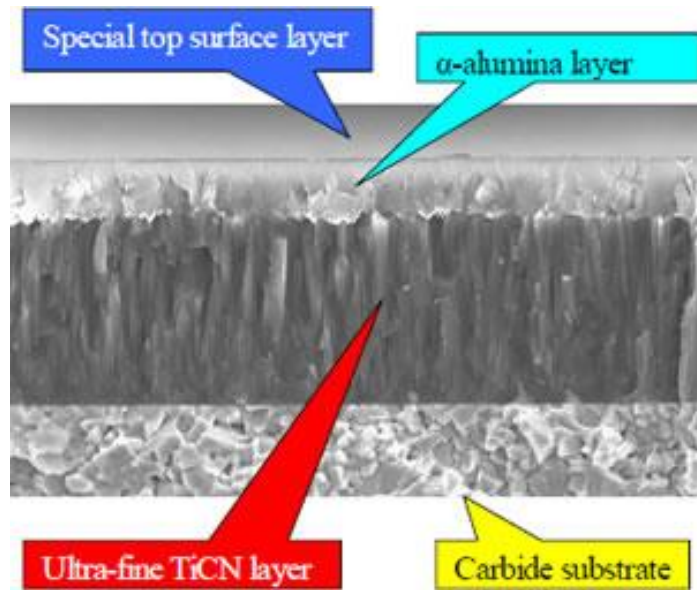
- Semi-conductors and some electronic compounds.
- Tools, bearing materials and coating of other wear resist parts.
- Optic, optoelectronic and corrosion resist products.
- Monolithic parts, ultra fine powders and high strength fibers can be produced.
- Multilayer coatings can be obtained with CVD.

\_\_\_\_\_TiN (Provides slipperiness and has gold yellow colour. Layer thickness 2-3  $\mu\text{m}$ )

\_\_\_\_\_Al<sub>2</sub>O<sub>3</sub> (Thermal barrier layer)

\_\_\_\_\_TiC (Adhesive layer)

\_\_\_\_\_Substrate



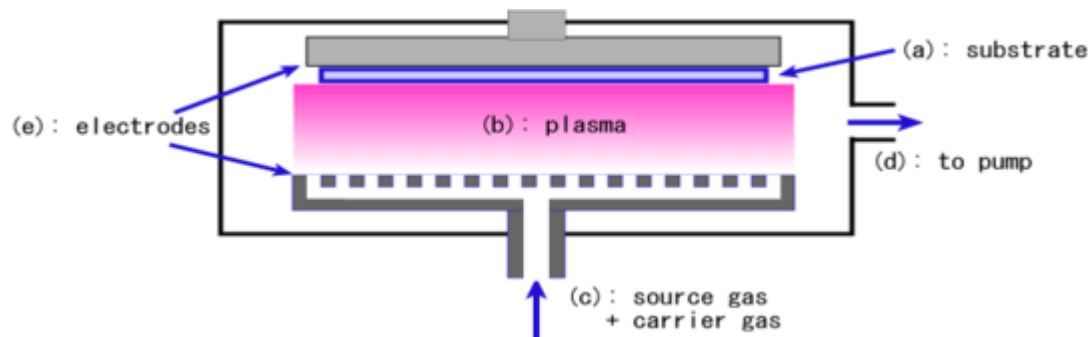
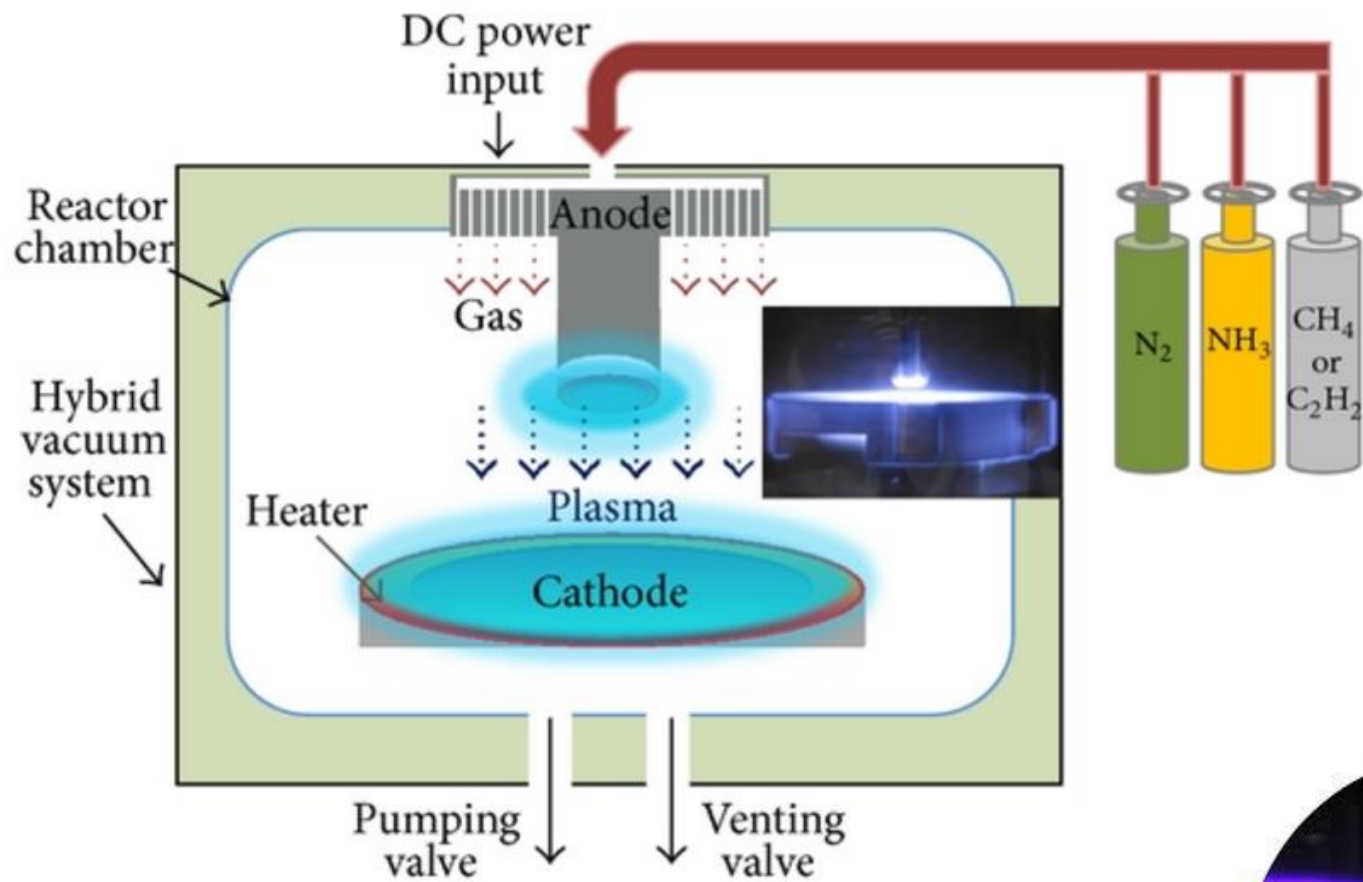
Multilayer CVD coating examples.

# Types of CVD

- Atmosphere pressured CVD (APCVD).
- Low pressured CVD (LPCVD).
- Plasma enhanced CVD (PECVD).
- Photon assisted CVD (PACVD)
- Metalorganic CVD (MOCVD).
- Epitaxial atomic layer growth (CBE) (Chemical beam epitaxy)

## **Plasma enhanced CVD (PECVD)**

- Plasma is used to achieve reactions which are impossible at low temperature.
- In this technique activation energy for decomposition of reactive particles and interactions of these particles with other particles to form deposition are provided with high kinetic energy electrons in the plasma.



## Major advantages of PECVD

- Low deposition temperatures (20-150 °C / 200-350°C).
- Deposition of unstable phases.
- Better control of purity and stoichiometry.
- Much better film adhesion and bonding strength.
- Suitable for deposition of insulating layers and temperature sensitive multilayer films.

## **Disadvantages of PECVD**

- Coatings occurred with low density and high imperfection content when compared to high temperature coatings.
- There is difficulty for deposition of pure metals.

# Applications of PECVD

- Si wafers of integrated circuits.
- DLC\* and DCC\*\* coatings for cutting tools.
- Fiber optic coatings
- Magnetic tape head coatings.

\*DLC: Diamond like carbon with shining black colour.

\*\*DCC: Diamond coated carbon.

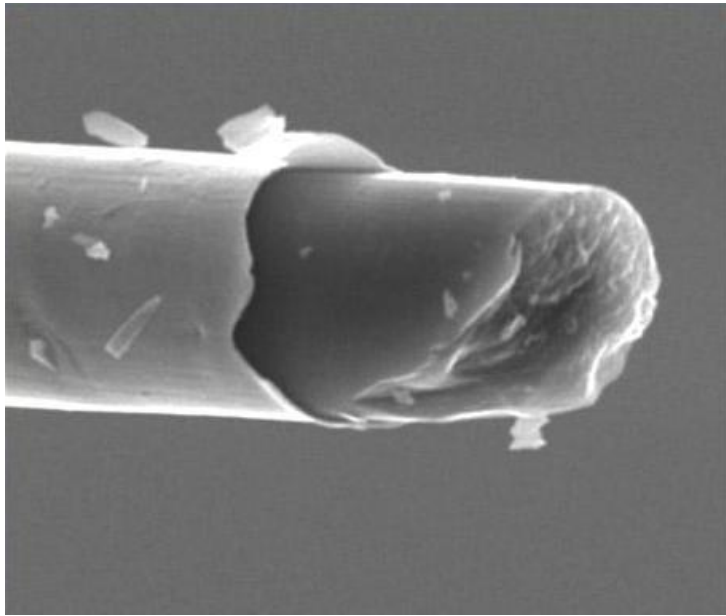


**DLC**

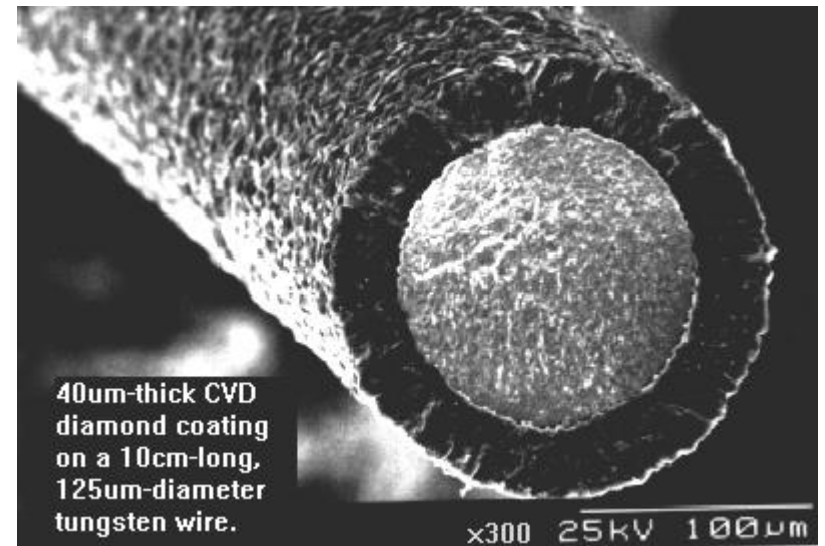


**DCC**





CVD nickel  
coated carbon  
fiber.



## Video links

- <https://www.youtube.com/watch?v=hkYb35e5JGo>
- <https://www.youtube.com/watch?v=j80jsWFm8Lc>
- <https://www.youtube.com/watch?v=1MFz0QToX6Q>
- <https://www.youtube.com/watch?v=HEATKNByyg0>
- <https://www.youtube.com/watch?v=xV32RrTu0ik>
- <https://www.youtube.com/watch?v=i-3SPiWEHo>
- <https://www.youtube.com/watch?v=UGFkgLZ6EVI>